Modelling amorphous materials via a joint solid-state NMR and X-ray absorption spectroscopy and DFT approach: application to alumina

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Understanding electronic structure is a crucial component in the development of many functional materials including semiconductors, transparent-conducting oxides, and batteries, and is necessarily directly dependent on their underlying atomistic structure. The elucidation of atomistic structure is impeded, both experimentally and computationally, by structural disorder, presenting a huge challenge for designing functional amorphous materials. Amorphous materials may be characterised through their local atomic arrangements using, for example, solid-state NMR and X-Ray Absorption Spectroscopy (XAS). By using these two spectroscopy methods to inform the sampling of configurations from ab initio molecular dynamics we devise and validate an amorphous model, choosing amorphous alumina to illustrate the approach due to its wide range of technological uses. Our model predicts two distinct geometric arrangements of AlO\textsubscript{5} coordination polyhedra and determines the origin of the pre-edge features in the Al K-edge XAS. We finally construct an average electronic density of states for amorphous alumina, and identify localized states at the conduction band minimum (CBM). We show that the CBM is comprised of Al 3s states and connect this localization and the presence of the pre-edge in the XAS.

Deconvoluting this XAS by coordination geometry reveals contributions from both AlO\textsubscript{5} and AlO\textsubscript{4} geometries at the CBM give rise to the pre-edge, which provides insight into the role of AlO\textsubscript{5} in the electronic structure of alumina. This work represents an important advance within the field of solid-state amorphous modelling, providing a method for developing amorphous models through comparison of experimental and computationally derived spectra, which may then be used to determine the electronic structure of amorphous materials.

Introduction

Atomistic quantum mechanical modelling has played a critical role in driving many of the advances made involving crystalline materials over the last two decades — originally in terms of rationalizing materials properties, but now increasingly in predicting and optimizing both materials and devices\textsuperscript{1–4}. A significant challenge, however, lies in applying the same quantum mechanical methods to amorphous materials\textsuperscript{4,5}, despite their increasing role in devices; these include dielectric layers in organic electronics, and as protective coatings across a range of materials\textsuperscript{6–10}. The challenge lies in capturing both the complexity of the local structure and the heterogeneity and structural variations that occur over a variety of length-scales. Amorphous structures lack the translational and point group symmetries present in crystalline materials, which enable calculations of increasingly large cells. It is also non-trivial to validate such a model against relevant experimental structural data, as symmetry allows structure solution from X-ray diffraction (XRD) experiments, while structure solution of amorphous materials relies on techniques such as Nuclear Magnetic Resonance (NMR) and X-ray Absorption Spectroscopy (XAS) to infer local structure. To understand and ultimately improve the electronic properties of an amorphous material, it is imperative to produce an accurate model of local atomic and electronic structure.

Recent progress in applying machine learning to this problem has enabled models of amorphous single element structures such as silicon, carbon, and phosphorus\textsuperscript{4,11–13}, as well as progress in some two-element systems including HfO\textsubscript{2} and Li\textsubscript{2}Si\textsubscript{3}\textsuperscript{\textsuperscript{14}}. In these methods, machine learning is applied to describe the atomic level interactions using training sets from first principles energy and force calculations; machine learned models therefore have comparable radial distribution factors, bond-lengths, and structure factors to first principles models with improved simulation time and length scales\textsuperscript{3}. However, their ability to predict spectral properties such as NMR and XAS with first principles accuracy is lacking; although ShiftML predicts NMR shifts for molecular solids, its nuclei are limited to C, H, N, O, and S\textsuperscript{15}. Similarly, XAS spectral lines for transition metal oxides are predicted using a random forest method but applied only to a set of known, crystalline, transition metal oxides\textsuperscript{16}. Clearly, there is a need for spectral predictions with first principles accuracy, which can be applied to amorphous materials.

Atomic layer deposited (ALD) alumina is one of the most widely used amorphous coating materials, as it is a model ALD system with well-understood surface chemistry\textsuperscript{17,18}. ALD alumina was first employed as a high-k dielectric and is present in applications across a range of electronic devices from solar cells to battery electrodes and field-effect transistors. Amorphous alumina (a-Al\textsubscript{2}O\textsubscript{3}) is a wide band-gap insulator which enables surface passivation, interface stability, and protects against degradation as a coating material\textsuperscript{6,8,19,20}. These properties have increased the capacity retention of Li-ion battery electrodes\textsuperscript{19–21}, enhanced the lifetime of perovskite solar cells\textsuperscript{6,22}, and improved the catalytic capabilities of metal-organic frameworks\textsuperscript{23,24}. Given its clear widespread...
applications, an atomic level model of a-Al2O3 would be indispensable to the device physics community.

This work presents a method for modelling the local structure of an amorphous material at the quantum mechanical level of accuracy, that is one which describes the electronic structure of an amorphous solid using first principles methods, which is then applied to a-Al2O3. This method utilizes both first principles calculations and high-quality spectroscopy to confirm the detailed electronic structure of a-Al2O3. The novelty of our approach lies in the integration of locally sensitive experimental techniques with spectroscopy calculated from first principles. We obtain NMR spectra at fields up to 1 GHz, which is the current state-of-the-art in solid state NMR and show that our DFT-based model contains the same structural features captured by these experimental measurements. The atomic level accuracy of this model enables us to identify two distinct five-fold coordination geometries present in a-Al2O3, and the orbital character of electronic states at the Al pre-edge of the absorption spectrum, which are unique to a-Al2O3. We calculate an average electronic density of states on our model, in a computationally efficient and accurate manner, thereby opening the door for further investigation into amorphous electronic structure.

**Methods**

**Experimental methods**

Substrates for ALD were washed with Acetone, Methanol/Ethanol, then deionized water and blow dried with N2 before deposition. Depositions were performed with a Picosun R200 Advanced ALD tool attached to an MBraun glovebox. At a chamber base pressure of approx. 12 hPa the substrates were heated to 150°C. Trimethylaluminum (TMAI, EpiValence Ltd, Electronic grade) was used as precursor gas, DI water as reactant and N2 as purging gas. For each cycle, corresponding to one layer, the substrates were first exposed to precursor gas (flow = 150 sccm), purged, then reactant gas (flow = 200 sccm) and finally the chamber was purged again which completes a cycle. Pulse and purge durations were 0.1 s and 10 s, respectively.

For synchrotron measurements, Al2O3 ALD films were deposited on pre-cut 3 mm x 3 mm Si substrates (Pi-KEM, Prime Grade, intrinsic dopant). The substrates originated from a diced 2 inch diameter Si(100) wafer (275±25 μm thick, >200 Ω·cm) single-side polished with a thermal dry oxide layer of 20nm±10 percent on both sides. Substrates with varying numbers of ALD layers were prepared, ranging from 2 to 1000. XAS measurements shown in this work were obtained from the 1000 layer sample. For NMR measurements more sample were required, so an 8 inch Si wafer (Picosun) was used and 1000 ALD layers were deposited. Al K-edge XAS total electron yield experiments were conducted at the I09 beamline at Diamond Light source (United Kingdom) in a total electron yield setup.

For NMR spectroscopy measurements, these were taken at three different fields 16.4 T, 11.8 T, and 23.5 T as outlined below. 16.4 T & 11.8 T: 27Al NMR spectra were acquired using Bruker 4 mm HXY MAS probes. 10 spectra were acquired using a regular one-pulse pulse program with a small flip angle (π/6) on Bruker 700 MHz (16.4 T) and 500 MHz (11.8 T) magnets with Avance III consoles. Two-dimensional 27Al 3QMAS (triple quantum MAS) NMR spectra were acquired on a Bruker 700 MHz (16.4 T) magnet. Quadrupolar pulse optimization was performed on γ-Al2O3 powder (Acros Organics). 23.5 T: 27Al NMR spectra were acquired using a Bruker 1.9 mm HXY MAS probe. Spectra were acquired using a rotor-synchronised (40 kHz $\equiv 2\tau = 50\mu$s) Hahn-echo spectrum with $p_2 = 2 \cdot p_1 = 5\mu$s ($\tau/2= 2.5\mu$s) on a Bruker 1.0 GHz (23.5 T) magnet with an Avance Neo console. The MAS NMR experiments were performed at sample spinning speeds of 14 kHz (16.4 T & 11.8 T) or 40 kHz (23.5 T). The spectra were externally referenced against AlF3 powder (-17 ppm 33) The NMR sample was obtained by scratching off the top layer deposited on the 8 inch wafer using a Wolfram carbide pen. The powder was packed into a 4 mm (16.4 T & 11.8 T) or 1.9 mm (23.5 T) ZrO2 rotor.

Bruker Topspin software was used for raw data handling and processing. The 27Al spectra were fitted with DMFIT software 26 to obtain integrated ratios and values of average $\delta_{\text{iso}}$, average $C_Q$ and $\Delta CS$ using the CzSimple model with d=5 for the Gaussian Isotropic Model (GIM) case. The best fit is obtained using the GIM case of the Czjzek model 27, corresponding to a distribution of local environments that lead to a spread of quadrupolar coupling constants and chemical shifts.

**First-principles spectroscopy**

Details of the methods used to generate the amorphous model are given in the following section, Amorphous model generation. All AIMD simulations were performed using VASP v5.4.1 28 in the NVT ensemble using a Nose-Hoover thermostat 29 with a plane-wave energy cutoff of 520 eV using projector-augmented wave pseudopotentials 30, and k-point sampling done only at the $\Gamma$ point. The specific pseudopotentials, parameters, and methods used to calculate the spectroscopy from first principles are described in this section.

Both the XAS and NMR spectra were calculated on each configuration in the model independently and the outputs were summed across configurations to calculate the total spectrum. All spectral calculations, and electronic density of states were calculated at a plane-wave energy cut-off of 1000 eV and a single k-point at $\Gamma$ in CASTEP v19.11 31. The CASTEP gauge-inducing projector augmented wave (GIPAW) method was used to calculate all NMR parameters 31,32, at the PBE functional level of theory using the on-the-fly generated CIB library of pseudopotentials. The NMR parameters were averaged over 45 configurations from ob initio molecular dynamics (AIMD) with 48 Al atoms in each cell totalling 2160 27Al NMR chemical shielding parameters for the a-Al2O3 model.

Quadrupolar effects to the NMR spectra were introduced using SIMPSON 33 to carry out spin-simulations at the same sample spinning speeds as the MAS NMR experiments of 14 kHz (16.4 T & 11.8 T) and 40 kHz (23.5 T). The quadrupolar coupling...
constants, isotropic shieldings and asymmetry parameters for each Al site were used from the output of the GIPAW NMR calculations. These spectra were obtained without including any broadening in the frequency spectrum and were subsequently broadened using a Gaussian broadening scheme to produce the spectra shown in Fig. 3. To calculate the 2D isotropic vs. quadrupolar shift, the central transition of the quadrupolar shift for MQMAS spectra was calculated as follows,

$$\sigma_{qs}(^{27}\text{Al}) = -\frac{3 \times 10^{4} \times C_{Q} \times \eta_{Q}}{v_{0}} (1 + \eta_{Q}^{2}/3)$$

where $v_{0}$ is the spectrometer frequency in MHz, and $\eta_{Q}$ is the asymmetry parameter of the electric field gradient. Both $C_{Q}$ and $\eta_{Q}$ were obtained from DFT calculations of the magnetic shielding parameters. A spectrometer frequency of 182.4 MHz for $^{27}$Al, corresponding to a 1H Larmor frequency of 700 MHz, was used for $v_{0}$.

First principles XAS calculations were carried out by specifying a single atom at which to calculate the absorption edges. One Al atom from each of the 45 configurations was selected at random, in order to obtain a set of atoms on which to calculate the spectra, such that the total 45 Al atoms were in coordination environments which were representative of the 50%, 38%, and 12% of Al(W,V,VI) environments present in experiment. For each configuration an XAS spectra was calculated using the core-hole pseudopotential method within CASTEP v19.11. To calculate the XAS for the Al K-edge, a pseudopotential with a 1s core-hole was placed on the randomly selected atom within the configuration and charged balanced by placing a total positive charge of +1 on the cell. The absorption spectra was calculated at a plane-wave energy cut-off of 1000 eV, using the HARD pseudopotential library in CASTEP v19.11. The absorption spectrum was produced by OptaDOs v2.1 and broadened using the adaptive broadening scheme. This spectrum was referenced using the method of Mizoguchi et al. such that the transition energy is referenced to the difference in energy between the ground state configuration of a-$\text{Al}_{2}O_{3}$ and the configuration which includes the core-hole pseudopotential.

Results

Amorphous model generation

Building an amorphous model typically involves a tradeoff between large supercells and classically described inter-atomic potentials, or small cell sizes at a quantum mechanical level of theory, and a limited description of the structure. Intuitively, a high-accuracy inter-atomic potential, large cell size model is the goal, however first principles quantum mechanical calculations using density-functional theory (DFT) scale as $O(N^{3})$ making these large cell size accurate calculations unfeasible. Previous models of amorphous alumina from first principles are on the order of 50 to 200 atoms, and any of observables such as electronic DOS or chemical shift consider only a single unit cell. Furthermore, these models typically compare to previous experimental work on amorphous alumina, rather than ensuring that the experimental conditions they are comparing to are consistent; given the known interdependence between structure and deposition conditions, especially in the case of amorphous alumina, a direct comparison is imperative, as we will show herein.

Our method, outlined in Fig. 1, uses experimentally driven directed sampling across a set of high-quality small cell size calculations from ab initio molecular dynamics (AIMD) to construct a model which reproduces experimentally known spectroscopic signatures, specific to ALD deposited a-$\text{Al}_{2}O_{3}$. The resultant model is a set of static configurations from AIMD which contains local orderings that are representative of the amorphous solid.

To build this model, we first generate a large set of AIMD simulations using a melt-quench technique which span a range of initial conditions (densities, equilibration temperatures, and rate of equilibration) as outlined in Fig. 1 Structure Generation. For each set of initial conditions, the AIMD simulations are repeated from different starting structures, thereby exploring additional local structural orderings. From these simulations, the static configurations from the final equilibrated 1000 timesteps of each simulation are considered. For the a-$\text{Al}_{2}O_{3}$ model, we generated 18 initial conditions, with 3 starting structures of 120 atoms each to generate a total of 54,000 static configurations. We simulated a-$\text{Al}_{2}O_{3}$ at densities of 3.18, 3.30, and 3.42 g/cm$^{3}$, equilibration temperatures or 300, 600, and 900 K, and using rates of equilibration which we refer to as a ‘cooling’ and ‘quenching’ scheme (the combination of these parameters resulting in 18 distinct initial conditions).

Each of these sets of initial conditions was specifically chosen based on literature of a-$\text{Al}_{2}O_{3}$ modelling to narrow the initial input size for our models. The range of densities 3.18, 3.30, and 3.42 g/cm$^{3}$ was chosen based on previous experimental literature on a-$\text{Al}_{2}O_{3}$ which suggests a range of possible densities between 3.05 to 3.40 g/cm$^{3}$ and further evidence that a density of 2.9 g/cm$^{3}$ is well below what is expected experimentally as this model from Lizarraga et al. contained AlO$_{3}$ environments which are not observed in experiment. A 120-atom model was used in order allow for computational efficiency, given the computational intensity of both NMR and XAS in DFT. Finally, the ‘quenching’ and ‘cooling’ schemes are in line with two distinct methods of amorphous model generation found in the literature. Although the cooling method is more commonly employed, as slower cooling rates have shown to give better results in line with experiment, the ‘quenching’ method used on a slab model of Al$_{2}O_{3}$ and Al showed consistent radial distribution functions to experiment, prompting us to explore this method.

In both equilibration schemes, 120 atoms with concentration Al$_{2}O_{3}$ were packed into a cubic box, using Packmol. The cell was then melted at a temperature of 4000K for 10 ps (5000 AIMD steps with a 2 fs time step). In the cooling scheme, the cell was then cooled to the desired equilibration temperature using the Nose-Hoover thermostat, whereas in the quenching scheme, the cell was immediately equilibrated from the melt for a further 10 ps. In this Structure Generation we have thus captured both the ergodicity across the range of
timesteps, and the randomness across the range of AIMD simulations for a-\(\text{Al}_2\text{O}_3\).

A comparison across all 54 simulations from AIMD of the radial distribution functions (RDF) for a-\(\text{Al}_2\text{O}_3\) compared to the Lamparter et al RDF from 1997 is shown in the Supplementary Information Fig. S3. Interestingly, a majority of the models with varying densities, equilibration temperatures, and cooling schemes have comparable RDFs with experiment, prompting a further narrowing of this initial set of data in order to obtain a model which is specific to the experimental ALD deposited a-\(\text{Al}_2\text{O}_3\).

In order to select a model which contains similar local structural information to the ALD deposited alumina, we further curate our set of 54 independent simulations from 18 different initial initial conditions using experimental information from NMR in a process known as Fingerprinting (Fig. 1). Each set of simulations at a given initial condition is averaged across the 3 AIMD simulations for that set of initial conditions (a total of 3000 static configurations for each set of initial conditions). From this data, the concentrations of Al coordination environments, four- five- and six-fold Al, are extracted and compared to experimental values of 50%, 38%, and 12% ± 2% concentration, respectively (Fig. S1, Fig. S2). These experimental coordination environment concentrations are extracted by fitting the 27Al NMR using the Czjzek model as described in the Experimental methods section. All sets of initial conditions that do not meet the tolerances of the experimental concentrations are then excluded, in order to determine the set of initial conditions which will capture the specific local properties of a-\(\text{Al}_2\text{O}_3\); this is our way of using more informative experimental information to narrow down the configuration space to those simulations that are most likely to capture experimental properties.

Of the 18 initial conditions considered, the fingerprinting step identifies two initial conditions which produce models with ratios of four-, five-, and six-fold Al coordination environments within error of the experimental data. These are the set of simulations run at 600K and 300K using the cooling scheme at a density of 3.18 \(g/cm^3\). The results for the 300K model are shown throughout the main text and the 600K results are shown in the Supporting Information with comparable resulting spectra from first principles. The other 16 models, while also within the initial range of possible experimental conditions, therefore likely do not compare to our specific ALD coating of 1000 layers of a-\(\text{Al}_2\text{O}_3\), but could possibly be used in future work to model other phases of a-\(\text{Al}_2\text{O}_3\) with varying coordination environments.

Finally, we can construct the amorphous model from the simulations with initial conditions which meet the Fingerprinting criteria, as a set of randomly selected static configurations. For each initial condition, a set of 15 configurations across the final 1000 timesteps are randomly chosen from each of the 3 AIMD simulations, to create a total of 45 static configurations which make up the amorphous model. This is a total of 120 atoms per cell x 45 configurations or 5400 atoms in the amorphous model distributed across smaller cells of 120 atoms from AIMD. In this step, a check was added to ensure that the 45 randomly selected configurations retained the same coordination environment ratios as the original fingerprinting step. These 45 configurations are combined and referred throughout as the amorphous model.
First-principles spectroscopy on a-\(\text{Al}_2\text{O}_3\)

For some desired property, \(X\), such as electronic density of states, we can calculate the average value of this property across these 45 static configurations \((N_c)\) as,

\[
X(N_c) = \sum_{i=1}^{45} X(N_c)
\]

This is analogous to an ensemble average of the property in which the probability of each configuration is equally likely, as we are in an amorphous solid with no symmetry equivalence. Herein we show that this amorphous model not only captures global properties such as coordination number, but also the specific local electronic properties predicted by experimental spectroscopy.

By calculating the ensemble average across configurations using the method outlined above, the average NMR and XAS spectra were calculated, and compared to experimental spectroscopy on a 1000 layer sample of ALD deposited a-\(\text{Al}_2\text{O}_3\). Reproducing these experimental signatures indicates that this model captures the local order, and electronic properties of the experimental amorphous phase.

The experimental \(^{27}\text{Al}\) 1D NMR spectrum shown in Fig. 2A shows 3 distinct peaks corresponding to disordered four-, five-, and six-fold coordinated (\(\text{Al}(IV), \text{Al}(V)\) and \(\text{Al}(VI)\)) \(\text{Al}\) environments with a ratio of 50%, 38%, and 12% ± 2% respectively. The presence of the \(\text{Al}(V)\) signal at 40 ppm and the low intensity of the \(\text{Al}(VI)\) signal at 11 ppm are strong indicators of the amorphous nature. \(^{27}\text{Al}\) NMR shows that Al(IV) and Al(V) both have large quadrupolar shifts in the MAS dimension. The distributions of Al environments are shown and broadening of 8 ppm is applied to the total NMR spectrum. Note that this x-axis is \(\delta_{\text{iso}}\), indicating that this is a plot of the isotropic shifts from each individual Al atom, rather than the quadrupolar lineshapes (shown in Fig. 3). This corresponds to the spectrum at an infinitely high magnetic field.

(D) Comparison of \(\delta_{\text{iso}}\) and \(\delta_{\text{q}}\) from GIPAW NMR where the second-order quadrupolar shift \((\delta_{\text{q}})\) is calculated using the method from \(^{60}\). This method again shows distortions in the quadrupolar dimension for both Al(IV) and Al(VI), which is consistent with the MQMAS in B. The distribution of \(\delta_{\text{q}}\) indicates that quadrupolar effects play a large role in the experimental 1D lineshape.
experimental 1D spectrum (Fig. 2C). A wide distribution of C\text{S} values and calculated quadrupolar induced shifts (\(\delta_{Q}\)) across Al sites which ranges from 10 to 20 MHz (Fig. 2D), with a wider range for both Al(IV) and Al(V) environments. The calculated isotropic shieldings and corresponding quadrupolar shifts show similar trends to experiment, indicating that the model captures these features from NMR. The spin-simulation tool SIMPSON\textsuperscript{33} was used to incorporate quadrupolar interactions at three fields (11.75 T, 16.44 T, 23.49 T) corresponding to the three fields at which the experimental NMR spectra (Fig. 3A) were obtained. The resulting spectra are shown in Fig. 3B and the quadrupolar nature of the Al(IV) and Al(V) environments is well described as evidenced by the sloping tails towards lower \(\delta_{Q}\) values, which are indicators of quadrupolar environments. Furthermore, trends at increasing field strengths are captured by both theory and experiment, with higher fields showing sharper peaks of the Al(IV, V, VI) environments, and a narrower overall spectral width.

One advantage of calculating the NMR spectrum from first principles, is that the calculations retain an individual spectrum for each atom in the model. In this way, we can construct spectra based on atom-specific coordination environments. Using a crystal-symmetry metric (CSM)\textsuperscript{51}, a measure of the relative distortion from perfect symmetry was extracted for each site in the model. A comparison of the CSM to isotropic chemical shift (Fig. 4), shows that the majority of tetrahedral sites are distorted (CSM > 4)\textsuperscript{51}, which agrees with the wide quadrupolar distribution of Al(IV) shifts in experimental MQMAS. Separating the spectra into the closest geometric environment, as shown in Fig. 3, determines that within the a-Al\textsubscript{2}O\textsubscript{3}, there exist two types of Al(V) environments, square pyramidal and trigonal bipyramidal; these sites combine to make the Al(V) peak in the 1D NMR at 40 ppm, with a range of site-specific shifts from 20 to 60 ppm. Given Al(V)s unique appearance in amorphous Al\textsubscript{2}O\textsubscript{3} phases, this identification of two geometries of Al(V) sites suggests that further work should involve identifying the role of each geometry in electronic devices. The first principles model of a-Al\textsubscript{2}O\textsubscript{3} enables the construction of these two sites’ spectra, where experimental NMR shows them as overlapping.

NMR is a method available for validating the local atomic structure while XAS is a measurement for probing the local electronic structure of a-Al\textsubscript{2}O\textsubscript{3}. The Al K-edge XAS spectrum shown in Fig. 5, exhibits three main features; a pre-edge feature (a) and two dominant broad peaks at 1565 eV (b) and 1570 eV (c) which are similar to those in Al-rich glasses\textsuperscript{52} and attributed to transitions in Al(IV) and Al(VI) respectively. The absorption edge for Al(V) lies between Al(IV) and Al(VI), and has no experimental reference. Calculating core-hole spectra for all Al sites in the amorphous model, determines the location of this Al(V) absorption edge between 1565 and 1570 eV (Fig. 5), and confirms the absorption energy of the Al(IV) and Al(VI) peaks, implying that the model’s electronic structure is consistent with the experimental a-Al\textsubscript{2}O\textsubscript{3}.
Experimental XAS spectra obtained from the ALD deposited sample compared to the calculated core-hole XAS. The experimental spectra is identified by the red line labeled Experiment, and is obtained from the 1000 layer ALD deposited sample. Three distinct features at 1562, 1565, and 1570 eV are denoted by dashed lines a, b, and c. The grey lines in the Total spectra show each individual spectra calculated at a single Al site in each configuration from the model, and the solid black line is the sum of those spectra. DFT calculated spectra separated by coordination environment are shown in the bottom four spectra; thin lines are individual spectrum, thick lines are the sum of each geometric site’s spectra. All Al(IV) sites were classified as tetrahedral, Al(V) sites were subdivided into trigonal bipyramidal and square pyramidal, and Al(VI) as octahedral. Dashed vertical lines indicate relevant peaks in the experimental spectra.

In addition to identifying the two main XAS peaks, the pre-peak at 1563 eV was also reproduced. A pre-edge is documented for α-Al₂O₃ at 1565 eV, which occurs because of transitions from the Js to Js states in Al [33]. While this transition is normally dipole forbidden, the presence of atomic vibrations results in distorted octahedral environments and bond lengthening which causes p-s mixing to occur and allow this transition. The pre-edge in α-Al₂O₃ is at 1562 to 1563 eV, both in experiment and in the calculated spectra, as shown in Fig. 5, and occurs in either tetrahedral Al(IV) sites or square pyramidal Al(V) sites. Similarly to the α-Al₂O₃ case, this pre edge is a result of site distortions at the Al(IV) site (Fig. S10)[33]. The calculated XAS spectra suggests a possible origin of this pre-edge feature, arising from Al(IV) sites as well as the absorption energy of the Al(V) peaks, which are masked in experiment, as their absorption energies overlap with transitions in Al(IV) environments.

The method of averaging observable properties across configurations can further be extended to a first-principles specific technique, the electronic density of states (eDOS). The α-Al₂O₃ eDOS is of particular interest, as this material is a coating layer in many electronic devices such as Li-ion batteries, semiconductors, and field-effect transistors. The eDOS, calculated as an average across the 45 configurations in the amorphous model (Fig. 6), confirms the experimentally predicted wide band gap insulating nature of this material. States at the valence band maximum (VBM) are O p type character, and states at the conduction band minimum (CBM) are Al s character. Interestingly, we identify two small peaks at the bottom of the conduction band at 3.2 and 4.2 eV which are low density, but highly localized states in this material.

Previous experimental XAS on the Al L₂,₃-edge [36] propose that the location of the CBM is governed by the charge transfer from Al to O atoms, specifically between the O 2p states at the VBM and Al 3s states at the CBM. The eDOS shown in Fig. 5 confirms these experimental assignments of the orbital character and is consistent across each of the 45 configurations in the α-Al₂O₃ model. Further, as Fig. 5 indicates, these localized states at the CBM, which appear as the pre-edge in the XAS, arise from both Al(IV) and Al(V) coordination geometries. The pre-edge feature in both coordination geometries is present at 1562 eV, making it impossible to distinguish the individual contribution from either of the two geometries experimentally. The ability to deconvolute the spectral features arising form either Al(IV) or Al(V) contributions is therefore a unique feature of calculating the XAS from first principles. While such deconvolution is routinely applied in crystalline systems [35–38], this result demonstrates the capability of performing a similar analysis using a joint NMR and XAS analysis on an amorphous material, and determining the orbital character of these states using first principles calculations of the eDOS.
Conclusions

Previous work\textsuperscript{3,59} implies that amorphous models require thousands of atoms in the unit cell or semi-infinite simulation times to fully capture local properties. We show that by averaging across AIMD simulations and incorporating experimental insight into the sampling approach, we produce a model of a-\text{Al}_2\text{O}_3 which exhibits the same local structural properties as captured by experimental NMR and the same electronic properties as captured by XAS.

By using first principles methods to generate a model of a-\text{Al}_2\text{O}_3 this enables the calculation of electronic properties, such as the eDOS, NMR and XAS, which is not possible using classical simulation methods. This is especially important for functional materials such as alumina, which are routinely used in electronic devices. We further demonstrate the importance of incorporating experimental insight at the model configuration sampling stage, as we describe a set of 54 different AIMD simulations, all with sensible initial conditions and RDFs, but only two of which had coordination environments within the experimental margin of error. This additionally underscores the need for having a specific experimental comparison metric when generating amorphous models; the results presented in this work are all with reference to one ALD deposited sample of alumina using the most relevant possible spectroscopy methods for characterization.

Given the capabilities of first principle methods used today, producing amorphous eDOS, and in turn NMR and XAS spectra as we have done in this work to understand the electronic structure of a-\text{Al}_2\text{O}_3, is certainly achievable for other amorphous systems. The method of averaging across static configurations from experimentally directed sampling of configurations from AIMD simulations can be applied to other amorphous systems and used to calculate electronic properties from first principles methods that are otherwise unattainable using large system sizes. We expect that given the transferability of this method, calculating these spectral properties, and potentially others will become the norm for simulations on amorphous solids, and especially in the field of device physics, encourage progress in fine tuning the electronic properties of these materials.

Author Contributions

AF Harper: Formal analysis, Writing - Original draft preparation, Data curation, Conceptualization. SE Emge: Investigation, Writing - review and editing. PCMM Magusin: Support with MQMAS setup and analysis, organization of 1 GHz measurements. CP Grey: Supervision, Resources, Writing - review and editing. AJ Morris: Supervision, Resources, Writing - review and editing.

Conflicts of interest

There are no conflicts to declare.

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Notes and references


